900V N-Channel MOSFETs

PMY09N90T

General Description

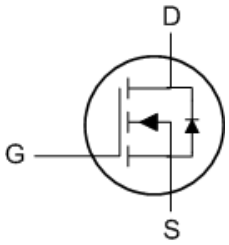
These N-Channel enhancement mode power field effect transistors are using advanced super junction technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply

BVDSS	RDSON	ID
900V	1.2Ω	9A

Features

- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*
- *Green Device Available*

TO-3P Pin Configuration



Applications

- *High efficient switched mode power supplies*
- *TV Power*
- *Adapter/charger*
- *Server Power*
- *PV Inverter / UPS*

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	900	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current – Continuous (T_C=25˚C)	9	A
	Drain Current – Continuous (T_C=100˚C)	5.7	A
I_{DM}	Drain Current – Pulsed[1]	36	A
EAS	Single Pulse Avalanche Energy[2]	1390	mJ
IAS	Single Pulse Avalanche Current[2]	16.7	A
P_D	Power Dissipation (T_C=25˚C)	240	W
	Power Dissipation – Derate above 25˚C	1.92	W/˚C
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	50	˚C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.52	˚C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	900	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.82	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=900V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=720V , V_{GS}=0V , T_J=125℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=4A	---		1.2	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	3	---	5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-9.4	---	mV/℃

Dynamic and switching Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=50V , V_{GS}=10V , I_D=1.3A	---	56	---	nC
Q_{gs}	Gate-Source Charge[3,4]		---	10	---	
Q_{gd}	Gate-Drain Charge[3,4]		---	6.4	---	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=30V , V_{GS}=10V , R_G=25Ω , I_D=0.5A	---	100	---	ns
T_r	Rise Time[3,4]		---	170	---	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	410	---	
T_f	Fall Time[3,4]		---	175	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	2395	---	pF
C_{oss}	Output Capacitance		---	170	---	
C_{rss}	Reverse Transfer Capacitance		---	20	---	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	1.45	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	9	A
I_{SM}	Pulsed Source Current		---	---	18	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=9A , T_J=25℃	---	---	1.4	V
t_{rr}	Reverse Recovery Time[3]	V_{GS}=0V,I_S=9A , dI/dt=100A/μs , T_J=25℃	---	550	---	ns
Q_{rr}	Reverse Recovery Charge[3]		---	6.5	---	nC

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=100V,V_{GS}=10V,L=10mH,I_{AS}=16.7A.,R_G=25Ω, Starting T_J=25℃.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

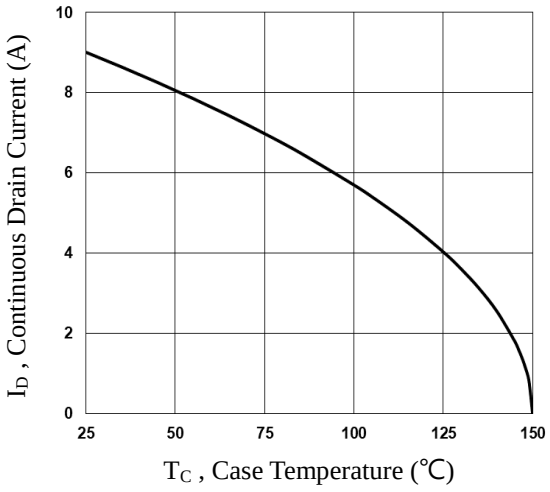


Fig.1 Continuous Drain Current vs. T_C

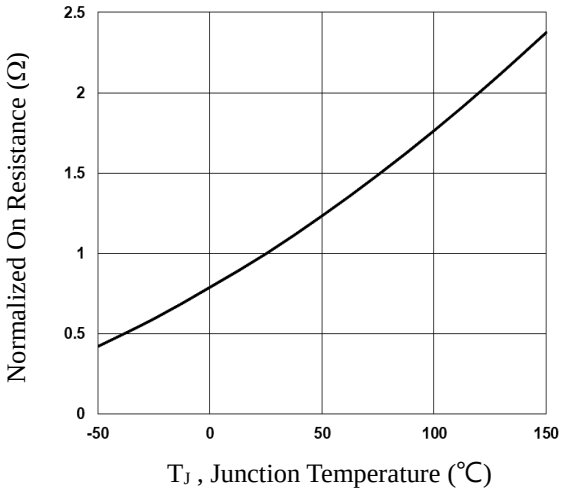


Fig.2 Normalized RDSON vs. T_J

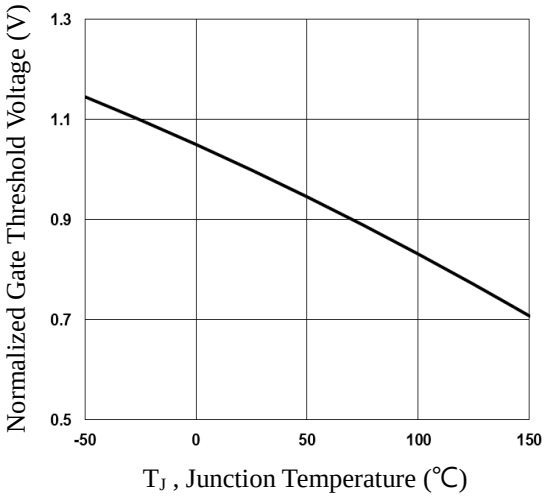


Fig.3 Normalized V_{th} vs. T_J

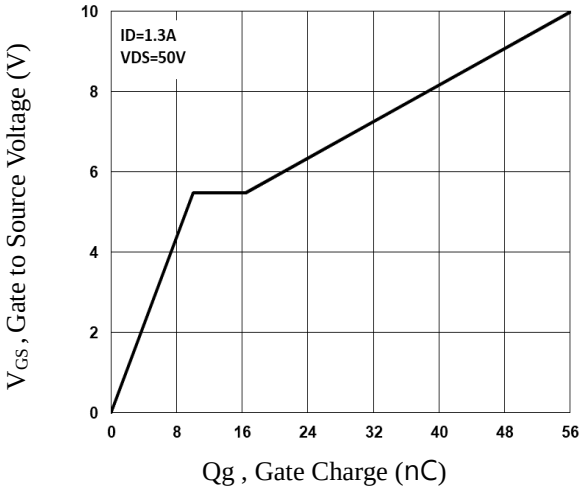


Fig.4 Gate Charge Waveform

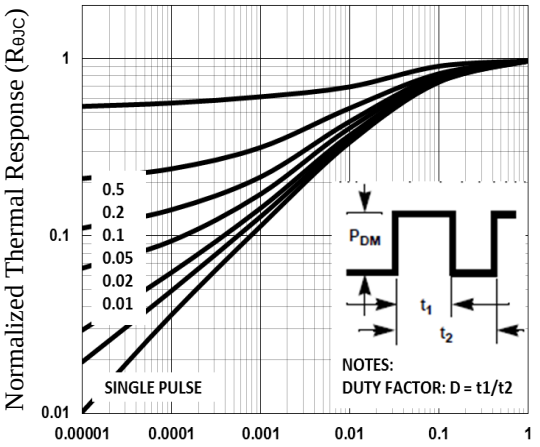


Fig.5 Normalized Transient Impedance

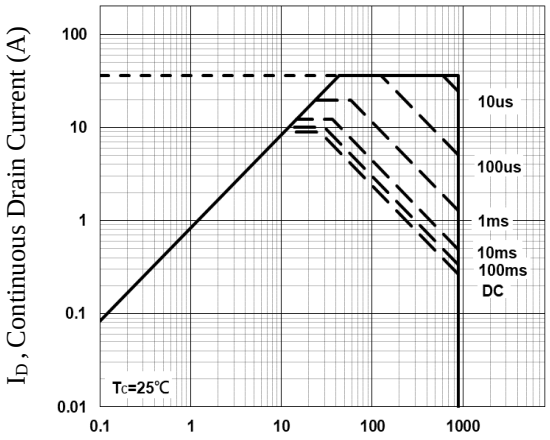


Fig.6 Maximum Safe Operation Area

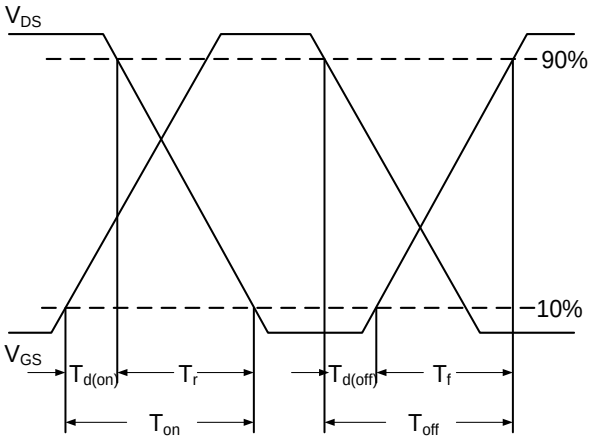


Fig.7 Switching Time Waveform

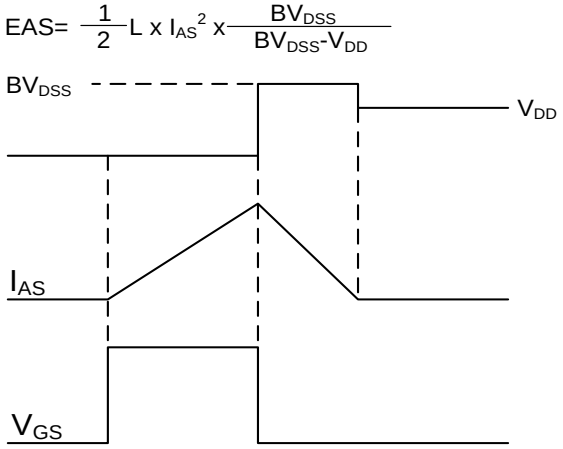
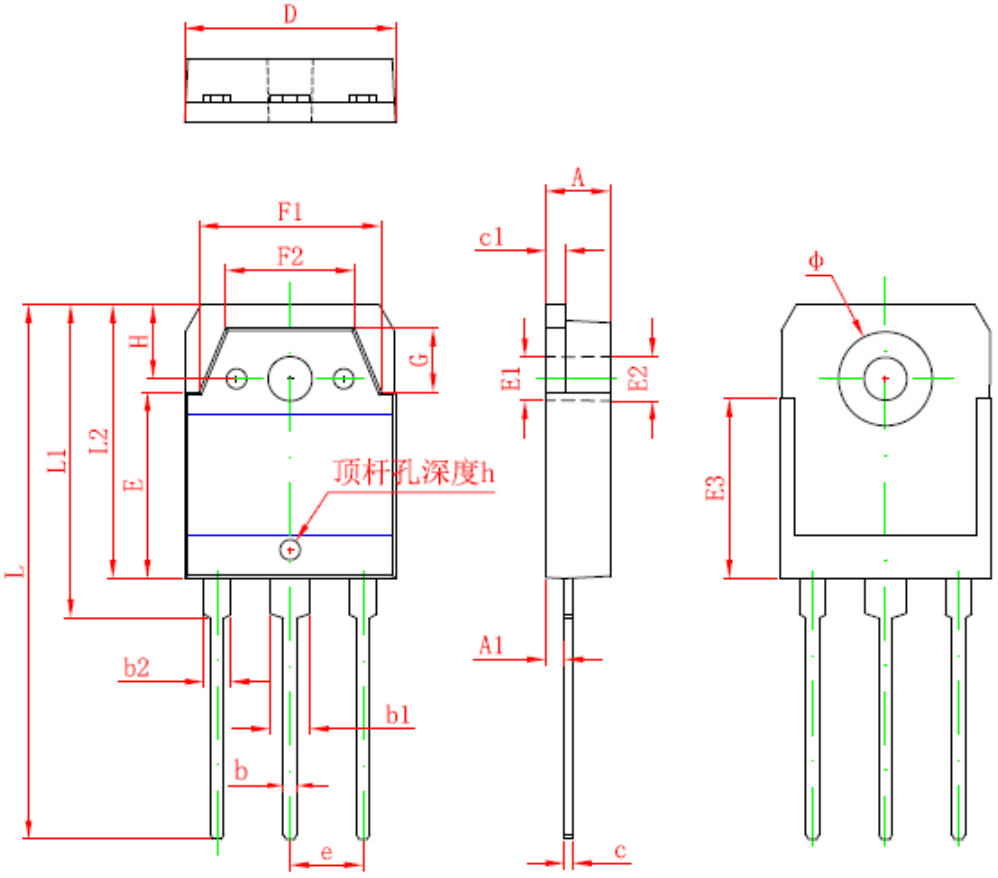


Fig.8 EAS Waveform

TO-3P PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.600	5.000	E3	13.450REF	
A1	1.200	1.600	F1	13.400	13.800
b	0.800	1.200	F2	9.400	9.800
b1	2.800	3.200	L	39.900	40.300
b2	1.800	2.200	L1	23.200	23.600
c	0.500	0.700	L2	20.300	20.600
c1	1.450	1.650	Φ	6.900	7.100
D	15.450	15.850	G	5.550	5.150
E	13.700	14.100	e	5.000REF	
E1	3.200REF		H	5.000REF	
E2	3.300REF		h	0.300	0.000